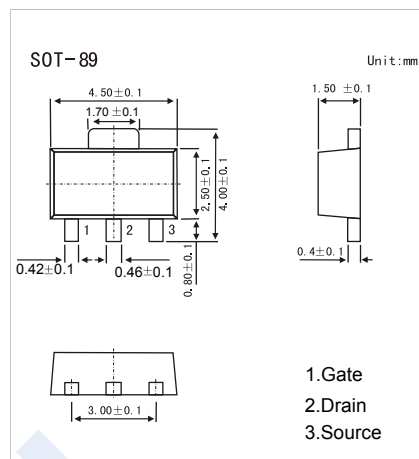
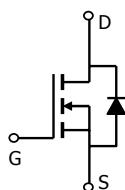


N-Channel MOSFET

KXF3055

■ Features

- $V_{DS} (V) = 60V$
- $I_D = 5.3 A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 60m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 80m\Omega$ ($V_{GS} = 4.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	5.3	A
Pulsed Drain Current	I_{DM}	30	
Power Dissipation	P_D	2	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

N-Channel MOSFET

KXF3055

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DS}	$I_D=250\ \mu A$, $V_{GS}=0V$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=48V$, $V_{GS}=0V$			0.1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS}=0V$, $V_{GS}=\pm 20V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=250\ \mu A$	1		2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$, $I_D=5.3A$			60	m Ω
		$V_{GS}=4.5V$, $I_D=4.7A$			80	
Forward Transconductance	g_{FS}	$V_{DS}=5V$, $I_D=4.7A$	6			S
Input Capacitance	C_{iss}	$V_{GS}=0V$, $V_{DS}=25V$, $f=1MHz$			800	pF
Output Capacitance	C_{oss}				250	
Reverse Transfer Capacitance	C_{rss}				60	
Total Gate Charge	Q_g	$V_{GS}=10V$, $V_{DS}=40V$, $I_D=4.7A$		9		nC
Gate Source Charge	Q_{gs}			2		
Gate Drain Charge	Q_{gd}			6		
Turn-On DelayTime	$t_{d(on)}$	$V_{DS}=25V$, $I_D=1A$, $R_G=6\ \Omega$			20	ns
Turn-On Rise Time	t_r				20	
Turn-Off DelayTime	$t_{d(off)}$				50	
Turn-Off Fall Time	t_f				20	
Diode Forward Voltage	V_{SD}	$I_S=2A$, $V_{GS}=0V$			1.25	V

■ Marking

Marking	KA
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